

L8	4	I4 and (silicide near10 electrode). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:00
L9	0	(recrystallized) near10 (silicide near10 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:00
L10	0	(recrystallized) with (silicide near10 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:00
L11	7	(recrystallized) with (silicide near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:00
L12	1	(recrystallized adj polysilicon) with (silicide near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:00
L13	2	(recrystallized adj polysilicon) same (silicide near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:00
L14	14	(recrystallized adj polysilicon) and (silicide near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:01
L15	3814	(capacitor) and (silicide near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:01
L16	801	(capacitor) with (silicide near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:02
L17	123	((capacitor) with (silicide near10 electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:02

L18	1	((capacitor) with (silicide near10 electrode)).clm. and (recrystallized adj polysilicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:02
L19	1	((capacitor) with (silicide near10 electrode)).clm. and (recrystallized adj polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:02
L20	1	((capacitor) with (silicide near10 electrode)) and (recrystallized adj polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:03
L21	60	capacitor and (recrystallized adj polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:03
L22	28	capacitor and (recrystallized adj polysilicon) and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:03
L23	8	capacitor and (recrystallized adj polysilicon) and (silicide near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:04
L24	57	capacitor and (recrystallized adj polysilicon) and (silicide 5 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:04
L25	8	capacitor and (recrystallized adj polysilicon) and (silicide near5 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:04
L26	2	capacitor and (recrystallized adj polysilicon) and (silicide near5 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:04
L27	1	capacitor and (recrystallized adj polysilicon) and (capacitor near5 silicide near5 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:04

L28	1	(recrystallized adj polysilicon) and (capacitor near5 silicide near5 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:04
L29	50	(capacitor near5 silicide near5 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:05
L30	101	(capacitor near10 silicide near10 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:05
L31	1	(capacitor near10 silicide near10 electrode).clm. and (recrystal\$6 near10 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:05
L32	1	(capacitor near10 silicide near10 electrode) and (recrystal\$6 near10 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:06
L33	1	(capacitor near10 silicide near10 electrode) and (recrystal\$10 near10 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:06
L34	75	(silicide near10 electrode) and (recrystal\$10 near10 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:06
L35	1	(capacitor with silicide with electrode) and (recrystal\$10 near10 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:06

L36	29	(US-20020028541-\$ or US-20030064567-\$ or US-20040155264-\$ or US-20050110114-\$ or US-20050199958-\$).did. or (US-4651184-\$ or US-4667217-\$ or US-4673962-\$ or US-4683486-\$ or US-4713678-\$ or US-4797373-\$ or US-4879585-\$ or US-4916504-\$ or US-4974051-\$ or US-5026656-\$ or US-5102817-\$ or US-5124766-\$ or US-5208657-\$ or US-5225697-\$ or US-5298782-\$ or US-5686335-\$ or US-5796150-\$ or US-5817548-\$ or US-5943593-\$ or US-6709904-\$ or US-4496964-\$).did. or (JP-60148163-\$).did. or (US-20050110114-\$ or KR-2004059433-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/11/27 20:07
L37	21	I36 and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:07
L38	1	I36 and (capacitor with electrode with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:07
L39	688	(capacitor near10 electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:08
L40	115	(capacitor near10 electrode near10 silicide).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:08
L41	59	(capacitor near5 electrode near5 silicide).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:08
L42	6	(capacitor near electrode near2 silicide).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:12

L43	30	(US-20020028541-\$ or US-20030064567-\$ or US-20040155264-\$ or US-20050110114-\$ or US-20050199958-\$).did. or (US-4651184-\$ or US-4667217-\$ or US-4673962-\$ or US-4683486-\$ or US-4713678-\$ or US-4797373-\$ or US-4879585-\$ or US-4916504-\$ or US-4974051-\$ or US-5026656-\$ or US-5102817-\$ or US-5124766-\$ or US-5208657-\$ or US-5225697-\$ or US-5298782-\$ or US-5686335-\$ or US-5796150-\$ or US-5817548-\$ or US-5943593-\$ or US-6709904-\$ or US-4496964-\$ or US-6400552-\$).did. or (JP-60148163-\$).did. or (US-20050110114-\$ or KR-2004059433-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/11/27 20:12
L44	29	l43 and (recrystallized near polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:14
L45	1	l43 and (thickness near10 (recrystallized near polysilicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:13
L46	1	l43 and ((thick or thickness) near10 (recrystallized near polysilicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:13
L47	15	l43 and (thickness near10 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:14
L48	11	l43 and (thickness near10 polysilicon near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:15
L49	69	(recrystallized adj polysilicon adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:15

L50	2	(thickness near10 (recrystallized adj polysilicon adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:16
L51	2	((thick or thickness) near10 (recrystallized adj polysilicon adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:16
L52	2	((thick or thickness) near10 (recrystallized adj polysilicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:16
L53	22	l43 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:17
L54	6	l43 and capacitor.clm. and (recrystallized near polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:17
L55	6	l43 and capacitor.clm. and (recrystallized near polysilicon) and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:17
L56	2	l43 and capacitor.clm. and (recrystallized near polysilicon) and (capacitor with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:18
L57	1	l43 and capacitor.clm. and (recrystallized near polysilicon) and (capacitor with electrode with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:18
L58	1	capacitor.clm. and (recrystallized near polysilicon) and (capacitor with electrode with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:18
L59	1	(recrystallized near polysilicon) and (capacitor with electrode with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:20

L60	0	(recrystallized near polysilicon) and (capacitor with electrode with (cobalt near silicide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:20
L61	30	(US-20020028541-\$ or US-20030064567-\$ or US-20040155264-\$ or US-20050110114-\$ or US-20050199958-\$).did. or (US-4651184-\$ or US-4667217-\$ or US-4673962-\$ or US-4683486-\$ or US-4713678-\$ or US-4797373-\$ or US-4879585-\$ or US-4916504-\$ or US-4974051-\$ or US-5026656-\$ or US-5102817-\$ or US-5124766-\$ or US-5208657-\$ or US-5225697-\$ or US-5298782-\$ or US-5686335-\$ or US-5796150-\$ or US-5817548-\$ or US-5943593-\$ or US-6709904-\$ or US-4496964-\$ or US-6400552-\$).did. or (JP-60148163-\$).did. or (US-20050110114-\$ or KR-2004059433-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/11/27 20:20
L62	0	l61 and (cobalt adj silicide) near10 (capacitor adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:20
L63	0	((cobalt adj silicide) near10 (capacitor adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:21
L64	9	((cobalt adj silicide) near10 (capacitor near2 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:22
L65	2430	((("cosi.sub.2") or (cobalt adj silicide) near10 (capacitor near2 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:22
L66	9	((("cosi.sub.2") or (cobalt adj silicide)) near10 (capacitor near2 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:22

L67	2	((("cosi.sub.2") or (cobalt adj silicide)) near10 (capacitor near2 electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 20:22
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